Resonant tunneling and Fano resonance in quantum dots with electron-phonon interaction

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Abstract

We theoretically study the resonant tunneling and Fano resonance in quantum dots with electron-phonon (e-ph) interaction. We exam ine the bias-voltage (V) dependence of the decoherence, using Keldysh Green function method and perturbation with respect to the e-ph interaction. With optical phonons of energy $!_0$, only the elastic process takes place when $eV < !_0$, in which electrons emit and absorb phonons virtually. The process suppresses the resonant amplitude. When $eV > !_0$, the inelastic process is possible which is accompanied by real emission of phonons. It results in the dephasing and broadens the resonant width. The bias-voltage dependence of the decoherence cannot be obtained by the canonical transformation method to consider the e-ph interaction if its ext on the tunnel coupling is neglected. With acoustic phonons, the asymmetric shape of the Fano resonance grows like a symmetric one as the bias voltage increases, in qualitative accordance with experimental results.

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I. INTRODUCTION

In sem iconductor quantum dots, preservation of quantum coherence is an important issue for the application to the quantum information processing. To examine the coherence, the transport measurements have been reported using an Aharonov-Bohm (AB) ring with an embedded quantum dot, as an interferometer. The AB oscillation of the current has been observed as a function of magnetic ux penetrating the ring. The conductance usually shows a Breit-W igner resonance of symmetric Lorentzian shape, as a function of gate voltage which changes the electrostatic potential in the quantum dot. This indicates that electrons pass by a discrete level in the quantum dot coherently by the resonant tunneling. The transmitted wave of the electrons interferes with the wave traversing the other arm of the ring (reference arm), which results in the AB oscillation.

When the higher-order interference between the waves is important, the resonant shape is modied. Kobayashi et al. have observed an asymmetric peak of the conductance, as a function of the gate voltage. This is ascribable to the Fano resonance, which is generally caused by the interference between a discrete level and the continuum of states. The Fano resonance is observable when the wave through a discrete level interacts with the wave traversing the reference arm su ciently before it goes out of the ring: A naive picture in the path integral form alism is as follows. An incident wave from the source is split into two arm s, one includes a quantum dot and the other is the reference arm, and meets at the other side of the ring. Som e part of the wave goes out to the drain and the rest goes back to the original point along both arms and interacts, and so forth. If the phase relaxation length, 1, is comparable with the size of the ring, the shortest paths dominantly contribute to the current and result in the AB oscillation. Then we observe the Breit-Wigner resonance, as a function of gate voltage, which re ects the amplitude of a wave through the quantum dot. If 1 is much larger than the ring size, the contribution from many paths modies the resonant shape to the Fano resonance; an asymmetric shape with peak and dip is produced by positive or negative interference on either side of the B reit-W igner resonance where the phase shift diers by from each other. In Ref. 3, the asymmetric shape of the current becomes a symmetric one when the bias voltage increases. This implies that the nite bias signi cantly reduces 1.

The resonances in the AB interferom eter have been theoretically studied by several

groups. 6,7,8,9,10,11,12,13,14,15,16 The electron-electron interaction has been investigated, which leads to the \Fano-K ondo e ect. 8,10 Few theoretical work, however, has been done for the decoherence in the transport under a nite bias. In our previous paper, we have considered the dephasing e ect in the reference arm phenomenologically on the Fano resonance. The dephasing e ect on the AB oscillation by the spin-ip has been studied (in the case of Breit-Wigner resonance) when an odd number of electrons are localized in the quantum dot. 6,9

In the present paper, we exam ine the decoherence in the resonances by the electron-phonon (e-ph) interaction. A lthough the e-ph interaction in quantum dots has been studied by several groups, 17,18,19,20,21,22,23,24,25 the bias-voltage dependence has not been clarified even in the Breit-W igner resonance. Hence we discuss the e-ph interaction under a nite bias in the Breit-W igner resonance as well as in the Fano resonance. The aim s and main results of our study are as follows.

(i) First of all, we study the elects of longitudinal optical phonons on the Breit-Wigner resonance. To calculate the current under a nite bias, we adopt the Keldysh Green function method 26,27 and consider the e-ph interaction by the perturbation expansion. 17,18 Within the second-order perturbation, we distinguish elastic and inelastic processes at zero temperature. When the bias voltage is smaller than the phonon energy $!_0$, only the elastic process takes place, in which electrons virtually emit and absorb phonons. This process does not cause the dephasing, but it suppresses the resonant peak height without any change of the peak width. When the bias voltage is larger than $!_0$, an inelastic process is possible, in which electrons actually emit phonons. This results in the dephasing and broadens the peak width.

(ii) In som e papers, ^{19,20,23,28} the e-ph interaction is treated by the canonical transform ation m ethod, in which e-ph interaction is considered exactly in the quantum dot, whereas itse ect on the tunnel coupling is disregarded. We calculate the Breit-Wigner and Fano resonances with optical phonons by the method. By comparison with the perturbation calculation, we not some problems with the canonical transformation method to obtain the bias-voltage dependence.

(iii) We exam interpreted the extra of acoustic phonons on the Breit-Wigner resonance and Fano resonance. For the purpose, we extend the self-consistent Born approximation to the nite-bias transport in the Keldysh Green function formalism. 17,18 We not strong suppression of

the peak height in the Breit-W igner resonance since both elastic and inelastic processes are possible even at low bias in the case of acoustic phonons. In the Fano resonance, we show that the asymmetric shape is signicantly in uenced so that the dip almost disappears. This is in qualitative agreement with the experimental results.³

Concerning (i), M arquardt and Bruder have studied the elastic and inelastic processes in sequential tunneling through two quantum dots in parallel (double-dot interferom eter). 24 They have discussed \renormalization e ect" in the elastic process and \dephasing" in the inelastic process. The former stems from the dierence between the ground state of an environment in the presence or absence of an electron in the quantum dots. The e ect reduces the e ective tunnel coupling between the quantum dots and leads. This is not the case in our resonant tunneling in which an electron virtually stays in a quantum dot, with em itting and absorbing phonons, in the elastic process. We do not not the reduction of the peak width, whereas the zero-point uctuation of the phonons decreases the resonant peak height.

The organization of the present paper is as follows. In Sec. II, we present our model for the AB interferom eter with an embedded quantum dot. The expression of the current is derived in terms of the retarded G reen function. Section III is devoted to the explanation of how to treat the e-ph interaction in the Keldysh G reen function formalism. The calculated results with optical phonons are shown in Sec. IV, whereas those with acoustic phonons are given in Sec. V. The conclusions are presented in Sec. VI.

II. MODEL AND CALCULATION METHOD

A. Model

Our model for the AB interferom eter is shown in Fig. 1. There are two paths between leads L and R, one path connects the leads through a quantum dot by t_L and t_R , and the other path connects the leads directly by W $e^{i'}$ (reference arm). The phase 'represents the magnetic ux in the ring. The bias voltage between the leads is given by $eV = t_L = t_R$, where $t_L = t_R$ is the chem ical potential in lead L (R). We $t_R = t_R$ and $t_R = t_R$ or $t_R = t_R$.

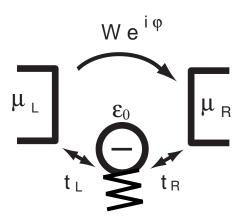


FIG. 1: Model that we adopt for an AB ring with an embedded quantum dot in the presence of electron-phonon interaction inside the quantum dot. The phase ' represents the magnetic ux in the ring.

the spin indices, the Hamiltonian for electrons is written as

$$H_{el} = H_{L} + H_{R} + H_{T} + H_{D};$$
 (1)

$$H_{L(R)} = X_{k} c_{L(R)k}^{y} c_{L(R)k}; \qquad (2)$$

$$H_{D} = "_{0}d^{y}d; \qquad (3)$$

$$H_{T} = (t_{L}c_{Lk}^{y}d + H x;)$$

$${}^{k}X$$

$$+ (t_{R}c_{Rk}^{y}d + H x;)$$

$$+ X^{k}$$

$$+ W e^{i'}c_{Rk}^{y}c_{Lk} + H x;; \qquad (4)$$

+
$$(t_R c_{Rk}^y d + H x;)$$

 X^k
+ $(W e^{i'} c_{Rk}^y c_{Lk} + H x;);$ (4)

where $c_{L(R)k}^{y}$ and $c_{L(R)k}$ denote the creation and annihilation operators of electron with m om entum k in lead L (R), respectively. W e assum e a single energy level $"_0$ in the quantum dot, with creation and annihilation operators being dy, d. The electron-electron interaction is neglected.

The strength of the tunnel coupling between the quantum dot and leads is characterized by the level broadening, = $_{L}$ + $_{R}$ w ith $_{L(R)}$ = 2 $t_{L(R)}^{2}$, where $_{R}$ is the density of states in the leads. We do no = 2 2 W 2 for the direct tunnel coupling between the leads. The transm ission probability through the reference arm is given by $T_r = 4 = (1 +)^2$. We exam ine the Breit-Wigner resonance without the reference arm by choosing = 0 and Fano-resonance by \pm 0.

We consider the e-ph interaction inside the quantum dot. The Hamiltonian for the interaction and that for the phonons are given by

$$H_{e ph} = {}^{X} M_{q} (a_{q} + a_{q}^{Y}) d^{Y}d;$$
 (5)

$$H_{ph} = X^{q}$$

$$!_{q}a_{q}^{y}a_{q}; \qquad (6)$$

respectively, where a_q^y (a_q) creates (annihilates) a phonon with momentum q. Unless otherwise noted, we will be setting ~ to unity. The coupling coe cient M $_q$ is written as

$$M_{q} = {}_{q}hd\dot{p}^{iq} \, {}^{r}\dot{p}di; \tag{7}$$

with $_{\rm q}$ being the amplitude of the e-ph interaction in the two dimensional electron gas. jdi represents the envelope function of electrons in the quantum dot. It should be noted that the electron-phonon interaction is negligibly small when jqj& 2 =L, where L is the size of the dot, owing to an oscillating factor of hdje jdi. Hence we can restrict the sum mation over q to be jqj. 2 =L in Eqs. (5) and (6).

The current is expressed as [see Appendix A]

$$I = \frac{2e}{h}^{Z} d! f_{L}(!) f_{R}(!)]$$

$$T_{r} + \frac{p}{T_{r}(1 T_{r})} \cos' ReG_{dd}^{r}(!)$$

$$\frac{1}{2}^{h} 1 T_{r} \cos^{2} \prime) T_{r} \operatorname{Tm} G_{dd}^{r}(!); \qquad (8)$$

where G $_{\mathrm{dd}}^{\mathrm{r}}$ (!) is the Fourier transform of the retarded G reen function of the quantum dot,

$$G_{dd}^{r}(t t^{0}) = i (t t^{0}) hfd(t); d^{y}(t^{0})gi;$$
 (9)

 f_L (!) [f_R (!)] is the Ferm i distribution function in lead L [R]. The level broadening is renormalized as $^{\sim}$ = = (1 +). = 4 $_L$ R = 2 is the asym m etric factor of the quantum dot.

We consider the tunnel couplings in H_T exactly before taking the e-ph interaction into account. In the absence of the interaction, the retarded G reen function is given by the equation-of-m otion method [see Appedendix A],

$$G_{dd}^{r(0)}(!) = \frac{1}{! \quad "_0 + \frac{1}{4} p \quad T_r \quad \infty s' + \frac{1}{2} }$$
(10)

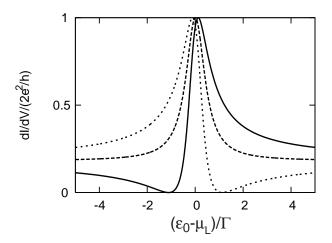


FIG. 2: The dierential conductance as a function of the dot level $"_0$ in the absence of e-ph interaction. The phase by the magnetic ux inside the ring is '=0 (dotted line), '==2 (dashed line), and '==(solid line). We x = 2 2 W $^2=0.05$ ($T_r=0.18$) and asym metric factor = 1.

The dierential conductance dI=dV at zero temperature is expressed as

$$dI = dV = \frac{2e^2}{h} T_r \frac{J + q_r}{u^2 + v^2 = 4};$$
(11)

where $u = L = \frac{1}{4} \frac{p}{T_r} \cos r$. This is an extended Fano form 5 with a complex parameter q_r ,

$$q_{\rm F} = \frac{r}{T_{\rm r}} p \frac{1}{1 T_{\rm r}} \cos' + i \sin' : \qquad (12)$$

Figure 2 shows the di erential conductance as a function of the dot level $"_0$, with = 1 and = 0.05 ($T_r = 0.18$). We observe a Fano resonance with dip and peak when ' = 0. With increasing ', the asymmetric resonant-shape changes to symmetric (' = = 2), and to asymmetric with peak and dip (' =). This is in agreement with the experimental results.

III. TREATMENT OF E-PH INTERACTION

We consider the e-ph interaction by the perturbation expansion; second-order perturbation in the case of optical phonons and self-consistent B orn approximation in the case of acoustic phonons. For the comparison, we also examine the B reit-Wigner resonance with optical phonons by the canonical transformation method. Optical phonons

A. Keldysh Green function

To exam ine the current under a $\,$ nite bias, we use the Keldysh G reen function form alism . The G reen function of the quantum dot is de ned by $\,$

$$G_{dd}(!) = \begin{pmatrix} G_{dd}^{t}(!) & G_{dd}^{<}(!) \\ G_{dd}^{>}(!) & G_{dd}^{t}(!) \end{pmatrix},$$
(13)

where the elements are the Fourier transforms of

$$G_{dd}^{t}(t \quad t^{0}) = iT hd(t)d^{y}(t^{0})i; \qquad (14)$$

$$G_{dd}^{t}(t \quad t^{0}) = i T hd(t) d^{y}(t^{0}) i;$$
(15)

$$G_{dd}^{<}(t \quad t^{0}) = ihd^{y}(t^{0})d(t)i;$$
(16)

$$G_{dd}^{>}(t \quad t^{0}) = ihd(t)d^{y}(t^{0})i;$$
(17)

respectively. The unperturbed G reen function, $G_{dd}^{(0)}$ (!), is de ned in the same way. They satisfy the D yson equation²⁸

$$G_{dd}(!) = G_{dd}^{(0)}(!) + G_{dd}^{(0)}(!)$$
 (!) $G_{dd}(!)$; (18)

where (!) is the self-energy by the e-ph interaction

$$(!) = {}^{0} {}^{t}(!) {}^{<}(!)_{A} :$$

$$(!) {}^{0} {}^{(!)} {}^{(!)} {}^{(!)} {}^{(19)}$$

We need the retarded G reen function G_{dd}^{r} (!) in Eq. (8) to obtain the transport properties. It is expressed as

$$G_{dd}^{r}(!) = G_{dd}^{t}(!) - G_{dd}^{c}(!)$$
: (20)

 $\mbox{G}_{\mbox{\scriptsize dd}}^{\,\, r}$ (!) follows the D yson equation of

$$G_{dd}^{r}(!) = G_{dd}^{r(0)}(!) + G_{dd}^{r(0)}(!)^{r}(!)G_{dd}^{r}(!);$$
 (21)

where the self-energy is given by

$$r(!) = r(!)$$
 (22)

Since $G_{dd}^{r(0)}$ (!) is given by Eq. (10), Eq. (21) yields the expression of

$$G_{dd}^{r}(!) = \frac{1}{! \quad "_{0} + \frac{1}{4} T_{r} \cos' + \frac{1}{2} i^{\sim} \quad r(!)}$$
(23)

By calculating $^{t}(!)$ and $^{<}(!)$, we obtain $^{r}(!)$ by Eq. (22) and hence $G_{dd}^{r}(!)$ by Eq. (23).

B. Perturbation expansion

In the second-order perturbation of e-ph interaction, the elements of the self-energy, Eq. (19), are written as

$$(!) = \frac{i}{2} \sum_{q}^{X} M_{q} \int_{0}^{2} d! G_{dd}^{(0)} (! !^{0}) D_{q} (q;!^{0})$$
(24)

(stands for t, t^0 , < , >). To obtain t^0 (!) and t^0 (!), we need t^0 (!), t^0 (!), t^0 (!) and t^0 0 reen functions of phonon, t^0 (q;!), t^0 (q;!).

 $G_{dd}^{<(0)}$ (!) is calculated using the equation-of-m otion method [see Appendix A] as

$$G_{dd}^{<(0)}(!) = G_{dd}^{r(0)}(!) \frac{i}{2} T_{r} \sin' [f_{L}(!) f_{R}(!)] + \frac{i}{(1+)^{2}} [(L_{L} + L_{R})f_{L}(!) + (L_{R} + L_{L})f_{R}(!)] G_{dd}^{a(0)}(!); \qquad (25)$$

where $G_{dd}^{r(0)}(!)$ is given by Eq. (10) and $G_{dd}^{a(0)}(!) = [G_{dd}^{r(0)}(!)]$. $G_{dd}^{t(0)}(!)$ is given by the relation, $G_{dd}^{t(0)}(!) = G_{dd}^{r(0)}(!) + G_{dd}^{<(0)}(!)$.

The Fourier transforms of phonon Green functions are

$$D^{t}(q;!) = 2 i N_{q} (! + !_{q}) + N_{q} (! + !_{q})] + \frac{1}{! \cdot !_{q} + i} \frac{1}{! + !_{q} i};$$

$$D^{<}(q;!) = 2 i [N_{q} + 1) (! + !_{q}) + N_{q} (! + !_{q})];$$
(26)

N $_{\rm q}$ denotes the phonon occupation number, 1=[exp(! $_{\rm q}$ =k $_{\rm B}$ T) 1]. We x the temperature at T = 0 in the calculations.

For the self-consistent Born approximation, $G_{dd}^{(0)}(! !^0)$ in Eq. (24) is replaced by $G_{dd}(! !^0)$ as

$${}^{t}(!) = \frac{i}{2} \sum_{q}^{X} M_{q} \int_{0}^{Z} d! \, {}^{0}G_{dd}^{t}(! ! {}^{0})D^{t}(q;! {}^{0}); \qquad (28)$$

and

$$(!) = \frac{i}{2} X M_q \int_{0}^{Z} d! G_{dd}^{(!)} (!) D^{(q;!)}$$
 (29)

From the D yson equation, Eq. (18), $G_{dd}^{<}$ (!) is expressed as

$$G_{dd}^{<}(!) = [1 + G_{dd}^{r}(!)^{r}(!)]G_{dd}^{<(0)}(!)[1 + a(!)G_{dd}^{a}(!)] + G_{dd}^{r}(!)^{<}(!)G_{dd}^{a}(!);$$
(30)

The substitution of Eqs. (23) and (25) into Eq. (30) yields

$$G_{dd}^{<}(!) = \frac{1}{[! \quad "_{0} + \frac{1}{4}^{P} \overline{T_{r}} \cos' \quad Re^{r}(!)]^{2} + [\frac{1}{2}^{\sim} \quad Im^{r}(!)]^{2}}$$

$$\frac{i}{2}^{\sim} \frac{T_{r} \sin' \left[f_{L}(!) \quad f_{R}(!)\right]}{[(L + R)f_{L}(!) + (R + L)f_{R}(!)] + (!)}$$

$$+ \frac{i}{(1 + R)^{2}} [(L + R)f_{L}(!) + (R + L)f_{R}(!)] + (!) : (31)$$

 G_{dd}^{t} (!) is obtained by Eq. (20), using $G_{dd}^{<}$ (!) in Eq. (31) and G_{dd}^{r} (!) in Eq. (23). We determ ine r (!) and $^{<}$ (!) by solving the equations self-consistently.

C. Canonical transform ation

For the comparison with the perturbative method, we exam in the canonical transform ation method. In this method, we decouple the e-ph interaction in Eq. (5) by a canonical transform ation of 8

$$H = e^{S}H e^{S}; (32)$$

$$s = d^{Y}d^{X} \frac{M_{q}}{!_{q}} (a^{Y}_{q} a_{q}):$$
 (33)

By the transform ation, the H am iltonians for electrons in the quantum dot, e-ph interaction, and phonons are rewritten as

$$H_{D} + H_{e ph} + H_{ph} = ["_{0}]^{X} \qquad (M_{q}^{2} = !_{q}) d^{y}d + X \qquad !_{q}a_{q}^{y}a_{q};$$
 (34)

The tunneling Hamiltonian, Eq. (4), is transformed to

$$H_{T} = \begin{array}{c} X \\ (t_{L}c_{Lk}^{y}d + H x:) \\ {}^{k}X \\ + (t_{R}c_{Rk}^{y}d + H x:) \\ X^{k} \\ + (W e^{i'}c_{Rk}^{y}c_{Lk} + H x:); \end{array}$$
(35)

where d and dy are renormalized operators of electrons,

$$d = e^{s}de^{s} = dX; (36)$$

$$d^{y} = e^{s}d^{y}e^{-s} = d^{y}X^{y}$$
 (37)

with

$$X = \exp \frac{X \frac{M_q}{!_q} (a_q^y a_q)}{!_q} :$$
 (38)

A first the decoupling of electron and phonon operators in Eq. (34), we take into account the e-ph interaction exactly, whereas we adopt an approximation for H_T : Electron operators, d and d^y , are replaced by d and d^y , disregarding the e-ph interaction in the tunnel couplings. The retraded G reen function G_{dd}^r (t t^0) is given in Appendix C.

IV. OPTICAL PHONONS

We begin with the case of longitudinal optical phonons. To illustrate the decoherence | zero-point uctuation e ect in the elastic process and dephasing e ect in the inelastic process | , we mainly discuss the e ects on the Breit-Wigner resonance in this section.

The amplitude of the e-ph interaction is described by the Frohlich-coupling²⁸

$$q = i \frac{1}{V} \frac{p}{\sqrt{\frac{4_{e} ph}{jqj}}} \frac{!_{q}}{2m !_{q}} \frac{1}{2m !_{q}};$$
(39)

$$_{e ph} = e^{2} \frac{m}{2!_{g}} \frac{1}{"(1)} \frac{1}{"(0)};$$
 (40)

where m is the electrice mass of electrons. "(1) and "(0) are the dielectric constants at high and low frequencies, respectively. V is the normalization volume. As a good approximation, we assume that all the phonons have the same energy! (Einstein model) since the wavenumbers are limited to a small range of jqj. 2 = L, when L is in the submicron scale. We do not be coupling strength of the e-ph interaction as

$$^{2} = {\stackrel{X}{\underset{q}{\text{m}}}} {\stackrel{2}{\text{m}}} :$$
 (41)

A. Breit-Wigner resonance

We exam ine the Breit-W igner resonance through a quantum dot without the reference arm (= 0, T_r = 0). We treat the e-ph interaction by the second-order perturbation. In Fig. 3, we plot the dierential conductance, dI=dV, as a function of the energy level " $_0$ in the

quantum dot. The bias-voltage is eV = 0.5 ($eV < !_0 = 2$; dashed line) and 3 ($eV > !_0$; solid line). A dotted line indicates the conductance in the absence of the e-ph interaction, where the conductance is independent of the bias. A subpeak at $"_0$ $!_0$ is seen only when $eV > !_0$, which corresponds to the em ission of a phonon.

When $eV < !_0$, a real process of phonon emission cannot take place at T = 0. Even in this case, the peak height is suppressed by the e-ph interaction. This is due to the elastic process in which electrons emit and absorb phonons virtually. It disturbs the coherent transport through the quantum dot and hence diminishes the resonant peak height. When $eV > !_0$, both elastic and inelastic processes are possible. The latter process makes the subpeak of the phonon emission, whereas the former process mainly suppresses the main peak, as discussed in the next section.

The position of the main peak is shifted by the e-ph interaction, regardless of $eV < !_0$ or $eV > !_0$. This is ascribable to the above-mentioned elastic process. The zero-point uctuation of phonons results in the renormalization of the energy level in the quantum dot, in addition to the suppression of the peak height.

The width of the main peak is in uenced by the inelastic process of phonon emission: it does not change when $eV < !_0$, whereas it is broadened when $eV > !_0$ although it is not clearly seen in Fig. 3. To discuss the width, we exam ine the retarded G reen function in Eq. (23). The peak width is determined by the imaginary part of the self-energy $^{\rm r}(!)$ in its denominator. When $eV < !_0$, Im $^{\rm r}(!) = 0$ in the range of integration, eV = eV, in Eq. (8). Hence the peak width is not changed. We conclude that the peak width is not in uenced by the elastic process of virtual emission and absorption of phonons in the resonant tunneling. This is in contrast to the sequential tunneling where the renormalization of the phonon state reduces the elective tunnel coupling between the quantum dot and leads. We hen $eV > !_0$, on the other hand, Im $^{\rm r}(!) \in 0$. At ! = eV,

Im
r
 (eV) = $\frac{^{2}}{4} \frac{^{2}}{(eV !_{0} "_{0})^{2} + ^{2}=4};$ (42)

which mainly determines the linewidth of the dierential conductance. Since Im^{-r} (eV) < 0, the linewidth is broadened by the e-ph interaction. The realem ission of phonons decreases the life-time of the dot state and, as a result, increases the peak width.

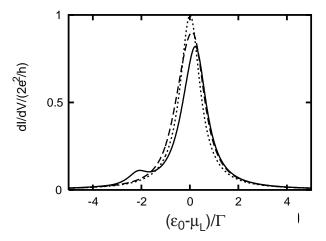


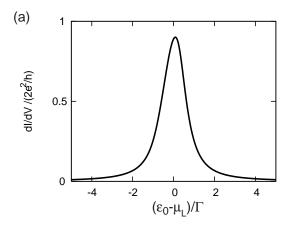
FIG. 3: The di erential conductance as a function of the dot level $^{"}_{0}$, in the case of B reit-W igner resonance (= 0, $T_{\rm r}$ = 0) with optical phonons. The asymmetric factor is = 1. The phonon energy is $!_{0}$ = 2, whereas the strength of e-ph coupling is = 0.8. The bias voltage is eV = 0.5 (dashed line) and 3 (solid line). Dotted line indicates the conductance in the absence of e-ph interaction.

B. Elastic and inelastic processes

To investigate the elastic and the inelastic processes more precisely, we perform the calculation considering the elastic process only. Among the four elements in the self-energy (!), Eq. (19), the diagonal elements, t and t, describe the elastic process while the o-diagonal elements, and h, represent the inelastic process, as discussed in Appendix B. Excluding the latter, the retarded G reen function is written as

$$G_{dd}^{r}(!) = G_{dd}^{r(0)}(!) + G_{dd}^{t(0)}(!)^{t}(!)G_{dd}^{r}(!)$$

$$+ G_{dd}^{<(0)}(!)^{t}(!)G_{dd}^{r}(!);$$
(43)



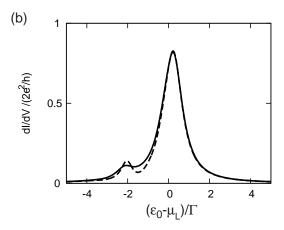


FIG. 4: Dierential conductance as a function of the dot level $"_0$ in the case of Breit-W igner resonance (= 0, T_r = 0) with optical phonons. The asymmetric factor is = 1. The phonon energy is $!_0$ = 2, whereas the strength of e-ph coupling is = 0.8. The bias voltage is (a) eV = 0.5 and (b) 3. The dashed line includes only the elastic process of e-ph interaction. The solid line includes both the elastic and inelastic processes. Note that dashed and solid lines are overlapped by each other in (a).

polaron in which an electron is coherently coupled with phonons. The resonant tunneling through a polaron level makes the subpeak. The polaron has a nite lifetime by the real emission of phonon. Hence the inelastic process broadens the subpeak as well as the main peak.

C. Fano resonance

Figure 5 shows the Fano resonance with optical phonons, in the presence of reference arm (x = 0.05, $T_r = 0.18$). The magnetic phase is (a) ' = 0, (b) ' = =2, and (c) ' = . The di erential conductance, dI=dV, is plotted as a function of the energy level " $_0$ in the quantum dot, when eV < ! $_0$ (dashed line) or eV > ! $_0$ (solid line). The dotted line indicates the non-interacting case.

The in vence of the e-ph interaction on the Fano resonance is qualitatively the same as that on the Breit-W igner resonance. When $eV < !_0$, only the elastic process takes place. Then we do not observe a subpeak of phonon emission. The zero-point uctuation of phonons reduces the resonant amplitude; both the resonant peak and dip are diminished.

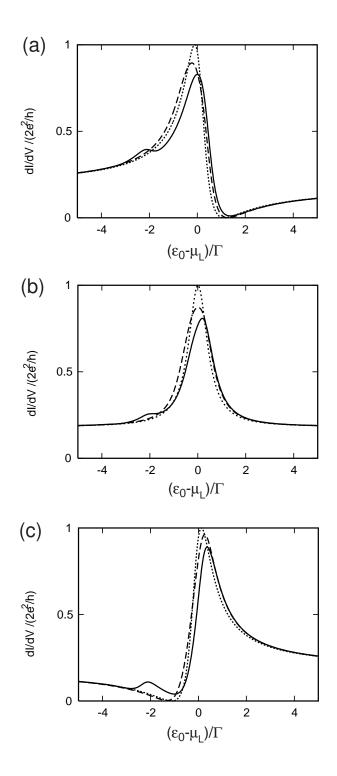


FIG. 5: D i erential conductance as a function of the dot level " $_0$ in the Fano resonance (= 0.05, $T_r = 0.18$). The asymmetric factor is = 1. The phonon energy is ! $_0 = 2$, whereas the strength of e-ph coupling is = 0.8. The magnetic phase is (a) ' = 0, (b) ' = =2, and (c) ' = . The bias voltage is eV = 0.5 (dashed lines) and 3 (solid lines). The dotted lines indicate the case in the absence of e-ph interaction.

The resonant width is not changed by the elastic process. When $eV > !_0$, a subpeak appears by the realem ission of phonon. The inelastic process broadens the width of main resonance.

The shape of the Fano resonance changes with magnetic phase ' in the same way as in Fig. 2. We not that the renormalization of the phase is negligibly small.

D. Calculation by canonical transform ation method

In this subsection, we consider the e-ph interaction by the canonical transformation m ethod. By the m ethod, the retarded G reen function is easily obtained as 23,28

$$G_{dd}^{r} (!) = e^{k(2N_{q}+1)} X^{1} Q_{1} \frac{q}{N_{q}(N_{q}+1)}$$

$$= \frac{e^{1!_{0}} = 2}{! ("_{0}) 1!_{0} + \frac{1}{4}P_{T_{r}} cos' + \frac{1}{2}};$$
(44)

where $J_1(x)$ are the Bessel functions. $k = (=!_0)^2$ and energy shift is $= ^2 = !_0$. At zero tem perature, $G_{dd}^r(!)$ is expressed as

$$G_{dd}^{r}(!) = e^{k} \frac{X^{0}}{!} \frac{k^{1}=1!}{! \quad ("_{0}) \quad 1! \quad 0 + \frac{1}{4} \frac{D}{T_{r}} \cos' + \frac{1}{2}}$$
(45)

The substitution of Eq. (45) into Eq. (8) yields the di-erential conductance. In the case of Breit-Wigner resonance (= 0, $T_r = 0$),

$$dI = dV = \frac{2e^2}{h} \sum_{k=1}^{X^0} \frac{2}{4} \frac{e^k k^k = 1!}{[L ("_0)]^2 + 2 = 4}$$
(46)

In the case of Fano resonance,

$$dI = dV = \frac{2e^2}{h}e^{k}T_r \frac{K^1}{1!} \frac{y_1 + q_r = 2\dot{j}^2}{1!};$$
(47)

where $\mathbf{u} = \mathbf{L} \quad (\mathbf{v}_0) \quad 1! \quad 0 + \frac{1}{4} \quad T_r \quad \infty s'$.

The calculated results are shown in Fig. 6, (a) B reit-W igner resonance and (b) Fano resonance. In the case of B reit-W igner resonance, the main peak (l=0) is given by the Lorentzian form with center at l=0 L=0, indicating the renormalization of the energy level. The peak height is reduced by the factor of l=0, whereas the width is xed at l=0. A subpeak is seen at l=0 L=0, corresponding to the emission of a phonon. Hence the polaron form ation can be described by this calculation method, similarly to the Tien-Gordon

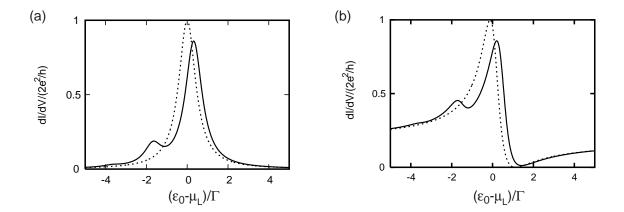


FIG. 6: Dierential conductance as a function of the dot level " $_0$ with optical phonons, calculated by the canonical transform ation method. The asymmetric factor is = 1. The phonon energy is $!_0 = 2$, whereas the strength of e-ph coupling is = 0.8. Dotted line indicates the dierential conductance in the absence of e-ph interaction. (a) C ase of resonant tunneling through a quantum dot (= 0, $T_r = 0$). (b) The case of Fano resonance (= 0.05, $T_r = 0.18$).

theory. The calculated results of Fano resonance can be understood in the same way as those of the Breit-W igner resonance.

We not some shortcomings of this method. (i) The bias-voltage dependence of the transport cannot be obtained. The dI=dV curve is independent of the bias in Eqs. (46) and (47). Hence the inelastic process of phonon emission takes place even when $eV < !_0$. The renormalization of the energy level by the e-ph interaction does not depend on the bias voltage. (ii) The resonant width of the main peak is not changed by the phonon emission. Hence the nite lifetime by the inelastic process is not considered properly. These are due to the approximation in the tunnel Hamiltonian. By the replacement of the electron operator d by d in H_T [Eq. (35)], we neglect the change of the phonon states accompanied by the tunnel processes.

V. ACOUSTIC PHONONS

Now we discuss the e-ph interaction with acoustic phonons. The amplitude of the e-ph interaction in Eq. (7) is described by the piezoelectric coupling, 22,31

$$j_{q}j = g \frac{{}^{2}c_{s}^{2}}{V_{q}j};$$
 (48)

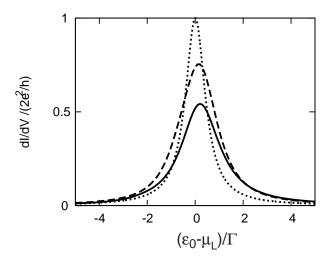


FIG. 7: Die erential conductance as a function of the dot level $"_0$ in the Breit-W igner resonance with acoustic phonons. The asymmetric factor is = 1. The coupling constant is g = 0.05, whereas the dot size is $L = c_s = (2)$. The bias voltage is eV = 0.5 (dashed line) and 2 (solid line). The dotted line indicates the conductance in the absence of e-ph interaction.

where g is a coupling constant and $c_{\rm s}$ is the sound velocity. The dispersion relation of the phonons is given by

$$!_{g} = c_{g} \dot{g} \dot{g} \dot{g} \tag{49}$$

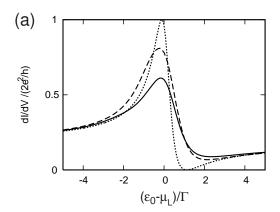
For the convenience of the calculation, we assume that jdje^{iq} jdij is given by

$$\text{fid}\dot{\mathbf{p}}^{iq} \, \, \, \, \dot{\mathbf{p}} \dot{\mathbf{j}} \dot{\mathbf{j}}^{2} = \frac{p}{2} \frac{1}{1^{-2}L^{2}} \frac{1}{q^{2} + (1=L)^{2}}$$
 (50)

in Eq. (7). For the calculation of e-ph interaction, we adopt the self-consistent Born approximation.

A. Breit-Wigner resonance

We begin with the B reit-W igner resonance in the absence of reference arm (= 0, $T_r = 0$). We set g = 0.05 and $c_s = 5000m = s$, which are the values in G aAs. 19,31 We xL = $c_s = (2)$: e. g.when = 0.1m eV, the dot size is L = 0.015 m (smaller than in Ref. [3]). The dierential conductance is plotted in Fig. 7, as a function of the energy level $^{"}_0$ in the quantum dot. The bias voltage is eV = 0.5 (dashed line) and 2 (solid line). In contrast to the case of optical phonons (Sec. IV), the inelastic process always exists, which is accompanied by the



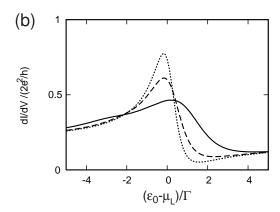


FIG. 8: Dierential conductance as a function of the dot level $"_0$ in the Fano resonance with acoustic phonons. We set = 0:05 ($T_r = 0:18$). The asymmetric factor is = 1. The coupling constant is g = 0:05. (a)The dot size is xed at $L = c_s = (2)$. The bias voltage is eV = 0:5 (dashed line) and 2 (solid line). The dotted line indicates the conductance in the absence of e-ph interaction. (b)We change the dot size as $L = c_s = (dotted line)$, $c_s = (2)$ (dashed line), and $c_s = (5)$ (solid line). The bias voltage is eV = 2.

real em ission of phonons. A subpeak structure is not observed since the acoustic phonon has a continuous spectrum.

We not the following elects of the e-ph interaction. (i) The resonant peak height decreases with increasing the bias voltage. As discussed in the previous section, this should be mainly ascribable to the elastic process. (ii) The peak width is more broadened with the bias voltage, which is due to the inelastic process. The emission of phonons results in the nite lifetime and hence an increase in the resonant width. (iii) The form of the Breit-Wigner resonance becomes asymmetric. The resonant peak is more suppressed on the side of " $_0 < _L$, than on the side of " $_0 < _L$. This may be explained as follows. When " $_0 < _L$, phonons can be emitted in the electron tunneling from lead L to the quantum dot, or in the tunneling from the dot to lead R.When " $_0 > _L$, phonons can be emitted only in the latter. Hence the decoherence works dierently on both sides of the resonance.

B. Fano resonance

Figure 8 (a) shows the Fano resonance with acoustic phonons, in the presence of reference arm (= 0.05, $T_r = 0.18$). The bias voltage is eV = 0.5 (dashed line) and 2 (solid line).

A subpeak structure is not seen as in the Breit-Wigner resonance with acoustic phonons.

The e-ph interaction decreases the resonant amplitude, whereas it increases the resonant width, rejecting the realem ission of phonons. These elects are more prominent with larger bias. Particularly, the resonant dip becomes almost invisible with high bias and as a result, the asymmetric shape of the Fano resonance grows like a symmetric one. Although this is in qualitative accordance with the experimental results, the resonant peak is still in an asymmetric form even in a smaller size of quantum dots (with stronger e-ph interaction, as discussed below) than in the experiment. To explain the experimental results quantitatively, we would have to consider the e-ph interaction in the reference arm as well as inside the quantum dot. The other dephasing elects, e.g. spin-ip of a localized electron in the quantum dot, might be also important.

We change the size of the quantum dot, L, in Fig. 8 (b): $L=c_s=$ (dotted line), $c_s=(2)$ (dashed line), and $c_s=(5)$ (solid line). The bias voltage is xed at eV=2. With an decrease in the dot size, them atrix element hdje iq ridi in the coupling coe cient M q increases [see Eq. (50)]. In consequence, the elect of e-ph interaction is enhanced. The gure indicates an aller amplitudes and wider widths of the resonance in smaller quantum dots.

VI. CONCULSIONS

We have investigated the Breit-Wigner resonance and Fano resonance in quantum dots with e-ph interaction. Using Keldysh Green function method and perturbation with respect to the e-ph interaction, we have obtained the bias-voltage (V) dependence of the decoherence.

W ith optical phonons of energy $!_0$, we distinguish elastic and inelastic processes. When $eV < !_0$, only the elastic process takes place in which electrons emit and absorb phonons virtually. The process suppresses the resonant amplitude, whereas it does not change the resonant width. We do not observe the renormalization of the tunnel coupling which has been discussed in the sequential tunneling. When $eV > !_0$, the inelastic process is possible, which broadens the resonant width. The process also makes a subpeak, as a function of the energy level in the quantum dot, corresponding to the realem ission of phonons. We cannot obtain any bias-voltage dependence of the decoherence when we consider the e-ph interaction by the canonical transformation method, neglecting its election the tunnel coupling.

W ith acoustic phonons, the suppression of resonant amplitude and broadening of the

resonant width are more prominent with an increase in the bias. In the Fano resonance, the resonant dip becomes almost invisible. The asymmetric resonant shape becomes like a symmetric one, in qualitative accordance with the experimental results. However, the model with e-ph interaction in the quantum dot only is not su cient for the quantitative explanation of the experiment.

In the present paper, we use the term of dephasing for the real em ission of phonons in the inelastic process. This is because the elastic process does not result in the dephasing, as discussed in Ref. 24. In the presence of reference arm, one might think that the dephasing e ect can be directly evaluated by calculating the amplitude of AB oscillation. But it is not correct. The e-ph interaction leads to the elastic and inelastic processes in the quantum dot on one hand, it changes the ratio of the current through the reference arm to that through the quantum dot on the other hand. Hence the amplitude of the AB oscillation cannot measure the dephasing e ect correctly.

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APPENDIX A: EXPRESSION OF CURRENT

The current from $\mbox{lead}\ \mbox{L}$ to the quantum dot is given by the time derivative of the occupation number in $\mbox{lead}\ \mbox{L}$,

$$I_L = ehN_{T}i = ieh[H; N_L]i;$$
 (A1)

with N $_{\rm L}$ = $^{\rm P}$ $_{\rm k}$ $c_{\rm Lk}^{\rm y}.$ A straightforward calculation yields

Here, we have introduced lesser G reen functions, $G_{d;Lk}^{<}(t;t^0) = ihc_{Lk}^{y}(t^0)d(t)i$ and $G_{Rk^0;Lk}^{<}(t;t^0) = ihc_{Lk}^{y}(t^0)c_{Rk^0}(t)i$. In the energy representation,

$$I_{L}(!) = \frac{2e}{h}Re d! t_{L} G_{d;Lk}^{<}(!) + We^{i'} G_{Rk^{0};Lk}^{<}(!) :$$
 (A3)

The current from lead R to the dot, I_R , is obtained in the same way. In the case of non-interaction leads, we can express the current using the G reen function of the quantum dot only, as shown in the following.

Let us consider $G_{d;Lk}^{<}(!)$ in Eq. (A3). Using equation-of-motion method and analytic continuation rules, 29 $G_{d;Lk}^{<}$ (t t^0) is written as

$$G_{d;Lk}^{<}(t t^{0}) = dt_{1} t_{L} G_{dd}^{r}(t t_{1}) g_{Lk}^{<}(t_{1} t^{0})$$

$$+ t_{L} G_{dd}^{<}(t t_{1}) g_{Lk}^{a}(t_{1} t^{0})$$

$$+ W e^{i'} G_{d;Rk}^{r}(t t_{1}) g_{Lk}^{c}(t_{1} t^{0})$$

$$+ W e^{i'} G_{d;Rk}^{c}(t t_{1}) g_{Lk}^{c}(t_{1} t^{0})$$

$$+ W e^{i'} G_{d;Rk}^{c}(t t_{1}) g_{Lk}^{a}(t_{1} t^{0})$$

$$+ (A 4)$$

where $G_{d;Rk}^{r}$ (t t^{0}) = i (t t^{0})hfd(t); c_{Rk}^{y} (t^{0})gi, $G_{d;Rk}^{<}$ (t t^{0}) = ih c_{Rk}^{y} (t^{0})d(t)i, g_{Lk}^{a} (t t^{0}) = i (t^{+} t^{0})hf c_{Lk} (t); c_{Lk}^{y} (t^{0})gi, and $g_{Lk}^{<}$ (t t^{0}) = ih c_{Lk}^{y} (t^{0}) c_{Lk} (t)i. The Fourier transform ation yeilds

where $_{k}^{P}$ g_{Lk}^{a} (!) = i and $_{k}^{P}$ $g_{Lk}^{<}$ (!) = 2i f_{L} (!). A similar expression of $_{k}^{P}$ $G_{d;Rk}^{<}$ (!) is obtained in the same way. The expression together with Eq. (A.5) yields

$$\begin{array}{l} X \\ G_{d;L\,(R\,)k}^{\,<}\,(!\,) \,=\, \frac{i}{1+}\,\,[t_{L\,(R\,)}\,+\,i\,\,\,W\,\,e^{-i'}\,t_{R\,(L\,)}\,]G_{dd}^{\,<}\,(!\,) \\ \\ +\,\, \frac{2i}{1+}\,\,[t_{L\,(R\,)}f_{L\,(R\,)}\,(!\,)\,+\,i\,\,\,W\,\,e^{-i'}\,t_{R\,(L\,)}f_{R\,(L\,)}\,(!\,)\,]G_{dd}^{\,r}\,(!\,) \\ \\ +\,\, \frac{2i\,\,\,W\,\,e^{-i'}\,f_{L\,(R\,)}\,(!\,)}{1+}\,\,X \\ \\ \frac{2^{\,\,2\,\,2}W^{\,\,2}f_{R\,(L\,)}\,(!\,)}{1+}\,\,X \\ \\ G_{d;L\,(R\,)k}^{\,r}\,(!\,) \,: \end{array} \tag{A 6}$$

 $G_{d;L(R)k}^{r}$ (!), which appears on the right-hand side of Eq. (A6), is derived from the equation-of-motion method as

$$\begin{array}{lll} & & & & Z \\ G_{d;L\,(R\,)k}^{\,r}\,(t & t^0) & = & dt_1\,[t_{L\,(R\,)}G_{dd}^{\,r}\,(t & t_1)g_{L\,(R\,)k}^{\,r}\,(t_1 & t^0) \\ & & & + \,\,W\,\,e^{\,\,i'}\,G_{d\,R\,(L\,)k}^{\,r}\,(t & t_1)g_{L\,(R\,)k}^{\,r}\,(t_1 & t^0)]; \end{array}$$

where $g_{L(R)k}^r(t t^0) = i(t t^0)hf_{G_{L(R)k}}(t); c_{L(R)k}^y(t^0)gi$. From the Fourier transform, we obtain

Then we express $G_{d;L(R)k}^{<}$ (!) in term s of G_{dd}^{r} (!) and $G_{dd}^{<}$ (!).

 $G_{Rk^0;Lk}^{<}$ (!) in Eq. (A 3) can be expressed using G_{dd}^{r} (!) and $G_{dd}^{<}$ (!), by the same technique. As a result, the current I_L (!) [and also I_R (!)] is rewritten in terms of G_{dd}^{r} (!) and $G_{dd}^{<}$ (!) only. Finally we delete $G_{dd}^{<}$ (!) by taking a linear combination of them , $I = xI_L$ (1 x) I_R , and obtain Eq. (8).

The expression of unperturbed G reen functions, Eqs. (10) and (25), are obtained also by the equation-of-m otion m ethod:

$$G_{dd}^{r(0)}(t t^{0}) = \begin{cases} Z \\ dt_{1} [g_{d}^{r}(t_{1} t^{0}) \\ + t_{L} G_{d;Lk}^{r(0)}(t t_{1}) g_{d}^{r}(t_{1} t^{0}) \\ + t_{R} G_{d;Rk}^{r(0)}(t t_{1}) g_{d}^{r}(t_{1} t^{0})]; \end{cases}$$

$$(A 8)$$

$$G_{dd}^{<(0)}(t t^{0}) = \begin{cases} Z \\ dt_{1} [g_{d}^{<}(t_{1} t^{0}) \\ + t_{L} G_{d;Lk}^{r(0)}(t t_{1}) g_{d}^{<}(t_{1} t^{0}) \\ + t_{L} G_{d;Lk}^{<(0)}(t t_{1}) g_{d}^{a}(t_{1} t^{0}) \\ + t_{R} G_{d;Rk}^{r(0)}(t t_{1}) g_{d}^{a}(t_{1} t^{0}) \\ + t_{R} G_{d;Rk}^{<(0)}(t t_{1}) g_{d}^{a}(t_{1} t^{0}) \\ + t_{R} G_{d;Rk}^{<(0)}(t t_{1}) g_{d}^{a}(t_{1} t^{0})]; \end{cases}$$
(A 9)

where $g_d^{r,(a)}$ (t_1 t^0) and $g_d^{<}$ (t_1 t^0) are the G reen functions of the non-interacting electrons in an isolated dot,

$$g_d^{r(a)}(!) = \frac{1}{! \quad "_0 \quad i};$$
 (A 10)

$$g_d^{<}(!) = 2 \text{ in }_d (! "_0)$$
: (A 11)

 $n_{\rm d}$ is the distribution function of electrons in the dot. By the Fourier transform s, we obtain

$$G_{dd}^{r(0)}(!) = g_{d}^{r}(!) + t_{L}G_{d,Lk}^{r(0)}(!)g_{d}^{r}(!) + t_{R}G_{d,Rk}^{r(0)}(!)g_{d}^{r}(!);$$
(A 12)

$$-\infty$$
 t $\xrightarrow{\tau}$ ∞

FIG. 9: Complex-time contour on which nonequilibrium-Green function theory is constructed.

FIG. 10: D iagram s of the coutour-ordered G reen function G (; 0). Four diagram s correspond to the real-time G reen functions, G^{t} , G^{t} , G^{s} , and G^{s} , respectively.

$$\begin{split} G_{dd}^{<(0)}(!) &= g_{d}^{<}(!) \\ &+ t_{L} G_{d;Lk}^{r(0)}(!) g_{d}^{<}(!) + t_{L} G_{d;Lk}^{<(0)}(!) g_{d}^{a}(!) \\ &+ t_{R} G_{d;Rk}^{r(0)}(!) g_{d}^{<}(!) + t_{R} G_{d;Rk}^{<(0)}(!) g_{d}^{a}(!); \end{split} \tag{A 13}$$

By expressing $G_{d;Lk}^{(0)}(!)$, $G_{d;Lk}^{(0)}(!)$, $G_{d;Rk}^{(0)}(!)$, and $G_{d;Rk}^{(0)}(!)$ in term sof $G_{dd}^{(0)}(!)$ and $G_{dd}^{(0)}(!)$, we obtain Eqs. (10) and Eq. (25).

APPENDIX B:PERTURBATION EXPANSION

We discuss elastic and inelastic processes by the e-ph interaction, using the coutourordered G reen function. The contour-ordered G reen function of the quantum dot is de ned as

$$G_{dd}(; ^{0}) = ihT_{c} fSd()d^{y}(^{0})gi;$$
 (B1)

w here

$$S = T_{C} \exp i d_{1}H_{e ph}(_{1})$$
(B2)

is the contour-ordered S m atrix and d() = e^{iH} de iH . As shown in Fig. 9, the contour path C goes from t = 1 to t = 1 and goes back to t = 1.29 The time labels and 0 are located on the countour path. The contour-ordering operator $T_{\rm C}$ orders the operators following it in contour sence: O perators with time labels later on the contour are moved left of operators of earlier time labels.

FIG. 11: D iagram s of the coutour-ordered G reen function with self-energies. Solid lines indicate the contour-ordered G reen function of the dot electron, whereas dashed lines indicate the contour-ordered G reen function of phonons. Four diagrams correspond to the real-time G reen functions with self-energies of $^{\rm t}$, $^{\rm t}$, $^{\rm c}$, and $^{\rm b}$, respectively.

The contour-ordered G reen function, $G(; ^0)$, is related to the real-time nonequilibrium G reen functions, as shown in Fig. 10: $G^t(t t^0)$ when and 0 are on the upper branch, $G^t(t t^0)$ when and 0 are on the lower branch, and $G^>(t t^0)$ [$G^<(t t^0)$] when 0 is on the upper [lower] branch and is on the lower [upper] branch.

The contour-ordered G reen function obeys W ick's theorems in the contour-time order. In the second-order perturbation with respect to the e-ph interaction,

$$G_{dd}(;^{0}) = G_{dd}^{0}(;^{0}) + G_{dd}^{0}(;^{0}) + G_{dd}^{0}(;^{0}) + G_{dd}^{0}(;^{0});$$

$$G_{dd}(;^{0}) = G_{dd}^{0}(;^{0}) + G_{dd}^{0}(;^{0});$$

$$(_{1};_{2}) = X$$
 $M_{q}G_{dd}^{0}(_{1};_{2})D_{q}^{0}(q;_{1};_{2});$
(B 4)

w here

$$G_{dd}^{0}(_{1};_{2}) = ihT_{C} fd(_{0})d^{y}(_{0})gi_{el};$$
 (B 5)

$$D(q;_{1};_{2}) = ihT_{C}Q(_{1})Q(_{2})i_{ph};$$
 (B6)

with

$$Q() = a_q() + a_q^{Y}()$$
: (B7)

The bracket h i_{el} denotes the average over the states of dot electron in the absence of e-ph interaction and h i_{ph} denotes the average over those of phonons in the equilibrium state. Figure 11 shows four types of diagrams for the self-energies. Solid lines indicate the contour-ordered G reen function of the dot electron, whereas dashed lines indicate the contour-ordered G reen function of phonons. The diagrams can be divided into two types, one corresponds to the elastic process and the other corresponds to the inelastic process.

When $_1$ and $_2$ are on the same branch of contour path C, electrons emit (absorb) and absorb (emit) phonons. Therefore, the phonon state at t=1 is the same as at t=1. This is the elastic process in which the energy of electrons conserves. On the other hand, when $_1$ and $_2$ are on the dierent branches of the path, electrons emit or absorb phonons before t=1. This process indicates the real emission or absorption of phonons and hence corresponds to the inelastic process. Thus, the processes are inelastic.

In pratical calculations, we have adopted the real-time nonequilibrium G reen functions. These four diagrams correspond to self-energies of real-time nonequilibrium G reen functions t, t, t, and has labeled in Fig. 11. Note that our de nition of elastic and inelastic processes diers from that in Refs. 19 and 20.

APPENDIX C: CANONICAL TRANSFORM ATION

By the canonical transform ation of 20,23

$$H = e^{S}H e^{S}$$
 (C1)

and approximation of the replacement of H $_{\rm T}$ by H $_{\rm T}$, we can divide the H am iltonian into an

$$H_{el} = [T_0]^{X}$$
 $M_q^2 = !_q) d^y d + H_T + H_L + H_R$ (C2)

and phonon part H $_{\rm ph}$ = H $_{\rm ph}$. The retarded G reen function is decoupled as

$$G_{dd}^{r}(t t^{0}) = i (t t^{0})hfa(t); a^{y}(t^{0})g_{i_{0}}hX(t)X^{y}(t^{0})i_{oh};$$
 (C3)

w here

$$\mathfrak{C}(t) = e^{iH_{el}t} de^{iH_{el}t}$$
 (C4)

and

$$X^{\sim}(t) = e^{iH_{ph}t}X e^{iH_{ph}t}$$
: (C 5)

The bracket h i_{el} denotes the average over the states of dot electron in the absence of e-ph interaction and h i_{ph} denotes the average over those of phonons in the equilibrium state.

The electron part is calculated by the equation-ofm otion m ethod [sim ilar to Eq. (A8)] and the phonon part is calculated using Feym an disentangling.²⁸ W e obtain the retarded G reen function of the quantum dot

$$G_{dd}^{r}(t t^{0}) = G_{dd}^{r(e)}(t t^{0})F(t t^{0});$$
 (C 6)

w here

$$G_{dd}^{r(el)}(t t^{0}) = i(t t^{0}) \exp f i[^{"}_{0}] \qquad X M_{q}^{2} = !_{q}) \frac{1}{4} T_{r} \cos' t + \approx 2tg$$

and

$$F(t) = \exp[(t)]; \qquad (C7)$$

F (t) =
$$\exp[(t)];$$
 (C7)
(t) = $\frac{X}{q} \frac{M_q}{!_q} N_q (1 e^{i!_q t})$ (C8)

$$+ (N_q + 1) (1 e^{i!_q t})$$
: (C 9)

The Fourier transform of G_{dd}^{r} (t t^{0}) yeilds Eq. (44)

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